

Silicon PNP Power Transistors

2SA1644

DESCRIPTION

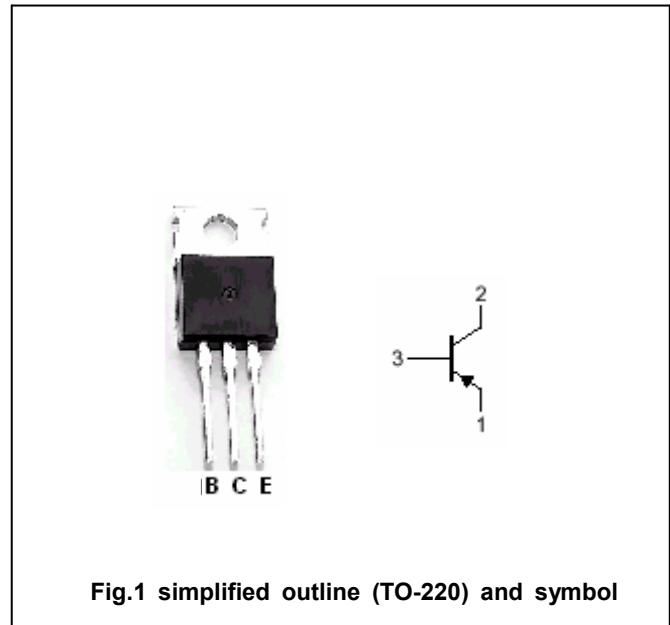
- With TO-220 package
- Fast switching speed
- Low collector saturation voltage

APPLICATIONS

- For use in switching power supplies,DC-DC converters,motor drivers,solenoid drivers, and other low-voltage power supply devices, as well as for high current switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-5	A
I_{CM}	Collector current-peak	$PW \leq 300\mu\text{s}$, duty cycle $\leq 10\%$	-10	A
I_B	Base current		-3	A
P_T	Total power dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_c=25^\circ\text{C}$	35	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.15A			-0.3	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-4A; I _B =-0.2A			-0.5	V
V _{BE sat-1}	Base-emitter saturation voltage	I _C =-3A; I _B =-0.15A			-1.2	V
V _{BE sat-2}	Base-emitter saturation voltage	I _C =-4A; I _B =-0.2A			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-10	μA
h _{FE-1}	DC current gain	I _C =-0.2A; V _{CE} =-2V	100			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-2V	100		400	
h _{FE-3}	DC current gain	I _C =-3A; V _{CE} =-2V	60			

◆ h_{FE-2} Classifications

M	L	K
100-200	150-300	200-400

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PACKAGE OUTLINE

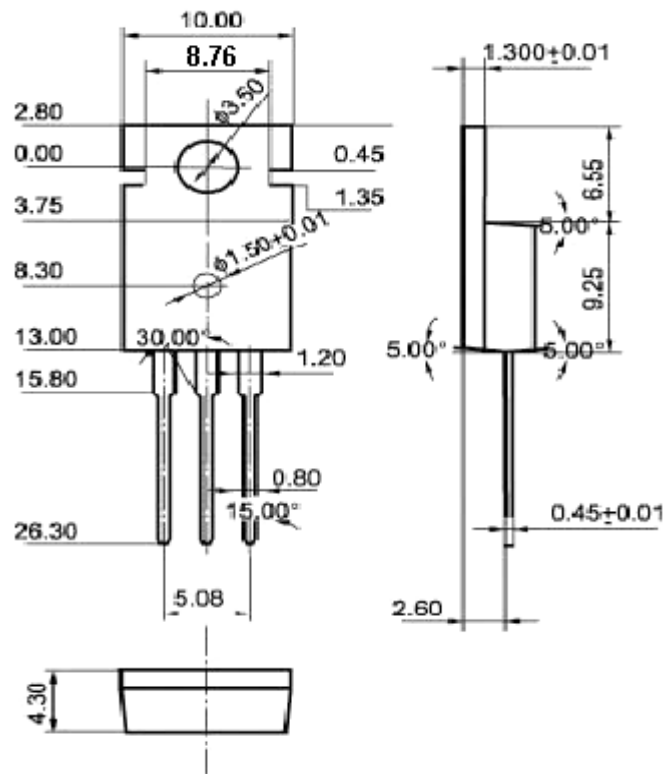


Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)